

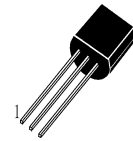
■ APPLICATIONS

General Purpose Transistors.

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	—Storage Temperature	-55~150°C
T _j	—Junction Temperature	150°C
P _C	—Collector Dissipation	625mW
V _{CBO}	—Collector-Base Voltage	75V
V _{CEO}	—Collector-Emitter Voltage	40V
V _{EBO}	—Emitter-Base Voltage	6V
I _C	—Collector Current	600mA

TO-92



1—Emitter, E
2—Base, B
3—Collector, C

■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CBO}	Collector-Base Breakdown Voltage	75			V	I _C =10 μA, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	40			V	I _C =10mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	6			V	I _E =10 μA, I _C =0
H _{FE}	DC Current Gain	100		400		V _{CE} =10V, I _C =150mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage			0.3	V	I _C =150mA, I _B =15mA
I _{CBO}	Collector Cut-off Current			10	nA	V _{CB} =60V, I _E =0
I _{EBO}	Emitter Cut-off Current			10	nA	V _{EB} =3V, I _C =0
f _T	Current Gain-Bandwidth Product	300			MHz	V _{CE} =20V, I _C =20mA
C _{ob}	Output Capacitance			8	pF	V _{CB} =10V, I _E =0, f=1MHz